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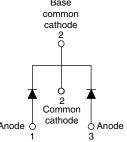
Vishay Semiconductors

# Hyperfast Rectifier, 2 x 15 A FRED Pt®



**TO-220AB** 

Diode variation



Common cathode

Base common cathode 2								
Anode 0	Com	) 2 nmon node	Anode 3					

#### **FEATURES**

- Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





HALOGEN **FREE** 

TO-220AB
2 x 15 A
300 V
0.85 V
See Recovery table
175 °C

## **DESCRIPTION / APPLICATIONS**

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage		$V_{RRM}$		300	V				
Average rectified forward current	per diode	I <sub>F(AV)</sub>	T <sub>C</sub> = 153 °C	15					
	per device			30	Α				
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	150					
Operating junction and storage temp	peratures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C				

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	300	-	-		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	1.0	1.25	V	
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C	-	0.85	0.95		
		V <sub>R</sub> = V <sub>R</sub> rated	-	-	40		
Reverse leakage current I <sub>R</sub>		T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	8	200	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 300 V	-	38	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH	



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	36		
Payeras rassyony time	t <sub>rr</sub>	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	30		
Reverse recovery time		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	33	-	ns	
		T <sub>J</sub> = 125 °C		-	48	-		
Dook receivery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.8	-	Α	
Peak recovery current		T <sub>J</sub> = 125 °C		-	6.5	-		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		=	46	-	nC	
		T <sub>J</sub> = 125 °C		-	160	-		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>	-65	=	175	°C			
Thermal resistance, junction to case per diode	$R_{thJC}$	-	-	1.4	°C/W			
Marking device		Case style TO-220AB 30CTH03						

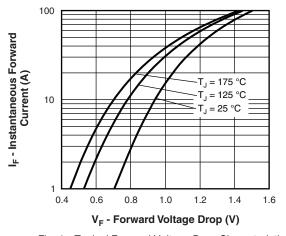


Fig. 1 - Typical Forward Voltage Drop Characteristics

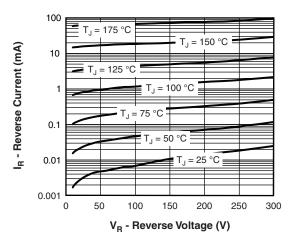


Fig. 2 - Typical Values of Reverse Current vs.
Reverse Voltage

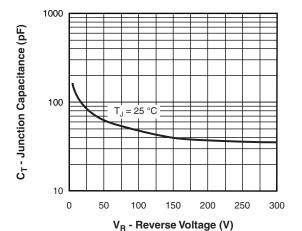


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

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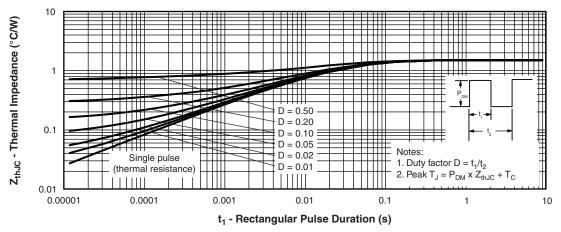


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

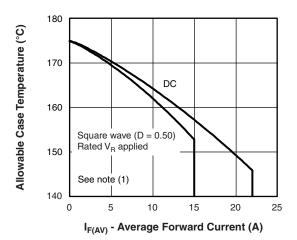


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

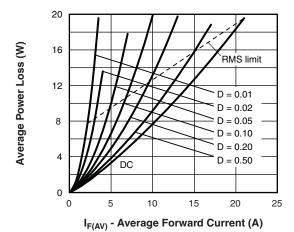


Fig. 6 - Forward Power Loss Characteristics

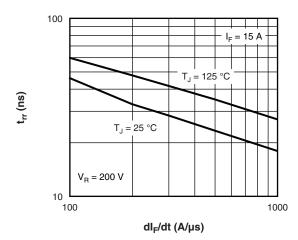


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

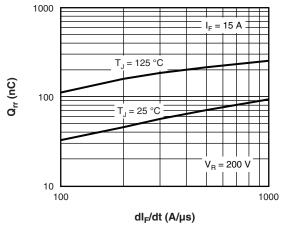


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

## Note

<sup>(1)</sup> Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>th,JC</sub>; Pd = Forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 6); Pd<sub>REV</sub> = Inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = Rated V<sub>R</sub>

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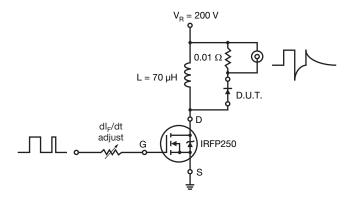
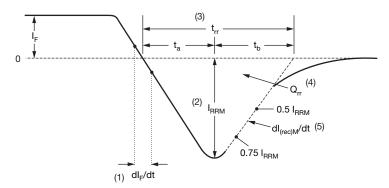


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) dI<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

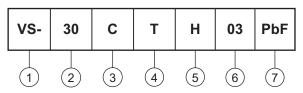
Fig. 10 - Reverse Recovery Waveform and Definitions

# VS-30CTH03PbF, VS-30CTH03-N3

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## **ORDERING INFORMATION TABLE**

**Device code** 



Vishay Semiconductors product

2 - Current rating (30 = 30 A)

Circuit configuration:

C = common cathode

4 - Package:

T = TO-220

5 - H = hyperfast recovery

Voltage rating (03 = 300 V)

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-30CTH03PbF	50	1000	Antistatic plastic tube					
VS-30CTH03-N3	50	1000	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS						
Dimensions	TO-220AB	www.vishay.com/doc?95222				
Dort marking information	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				



## Vishay Semiconductors

## **TO-220AB**

## **DIMENSIONS** in millimeters and inches



## Lead assignments

## **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

## Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		
		•	•	•	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



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